5

N-Channel Enhancement Mode Field Effect Transistor in a DFN3 3A-8L Plastic Package.

V_{DS} (V) = 40V
I_D = 40A (V_{GS} = ±20V)
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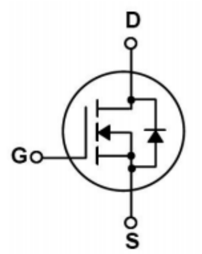
Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.



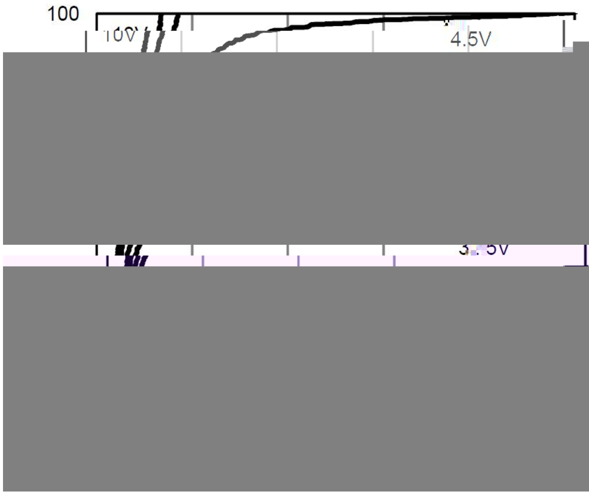
/ Marking

See Marking Instructions.

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_{g(10V)}$	V_{DS}=20V V_{GS}=4.5V I_D=20A		20		nC
Total Gate Charge	$Q_{g(4.5V)}$			8.5		
Gate-Source Charge	Q_{gs}			5.5		
Gate-Drain Charge	Q_{gd}			3		

/ Electrical Characteristic Curve



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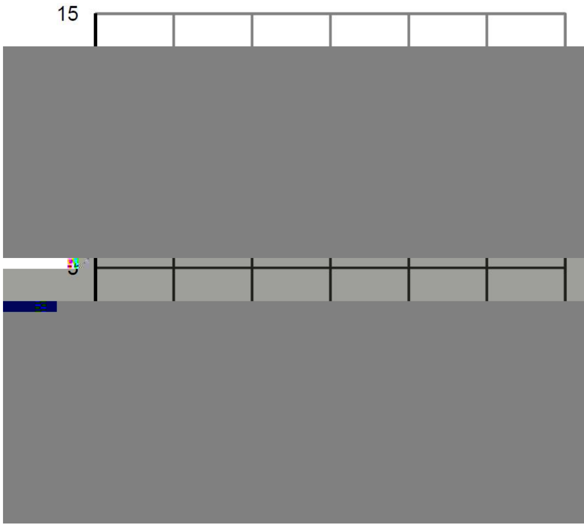

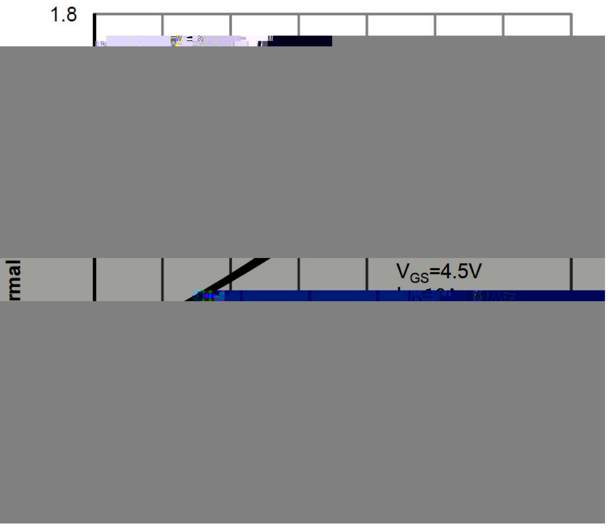

[redacted]

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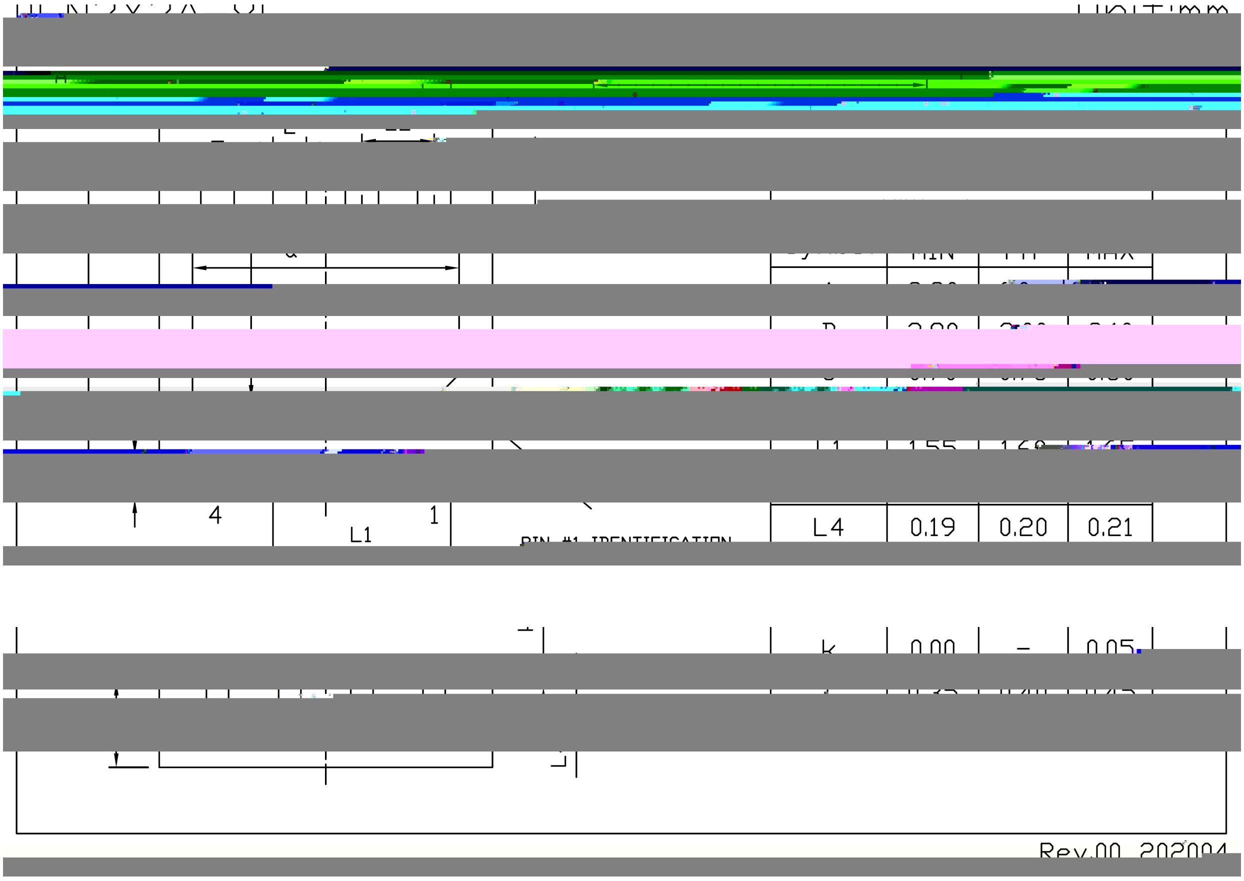
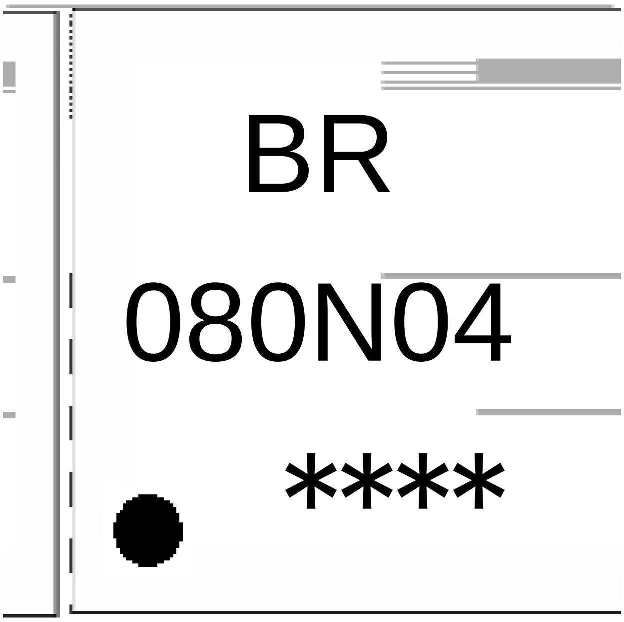
/ Electrical Characteristic Curve

/ Package Dimensions



/ Marking Instructions



BR

080N04

****

Note:

BR: Company Code.

080N04: Product Type

****: Lot No. Code, code change with Lot No.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)

	Note:
1 150 180 60 90sec;	1.Preheating:150~180℃, Time:60~90sec.
2 245±5 5±0.5sec;	2.Peak Temp.:245±5℃, Duration:5±0.5sec.
3 2 10℃/sec.	3. Cooling Speed: 2~10℃/sec.

/ Resistance to Soldering Heat Test Conditions

260±5℃ 10±1 sec. Temp.:260±5℃ Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type !	Units " # $	Dimension " % & (unit ' mm^3)